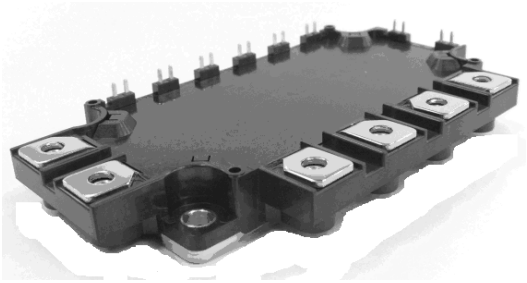
MITSUBISHI ELECTRIC

< IGBT MODULES >

CM75RX-34SA

HIGH POWER SWITCHING USE
INSULATED TYPE



sevenpack (3φ Inverter+Chopper Brake)

Collector current I_C ..... **75** A
Collector-emitter voltage V_{CES} ..... **1700** V
Maximum junction temperature T_{jmax} ..... **175** °C

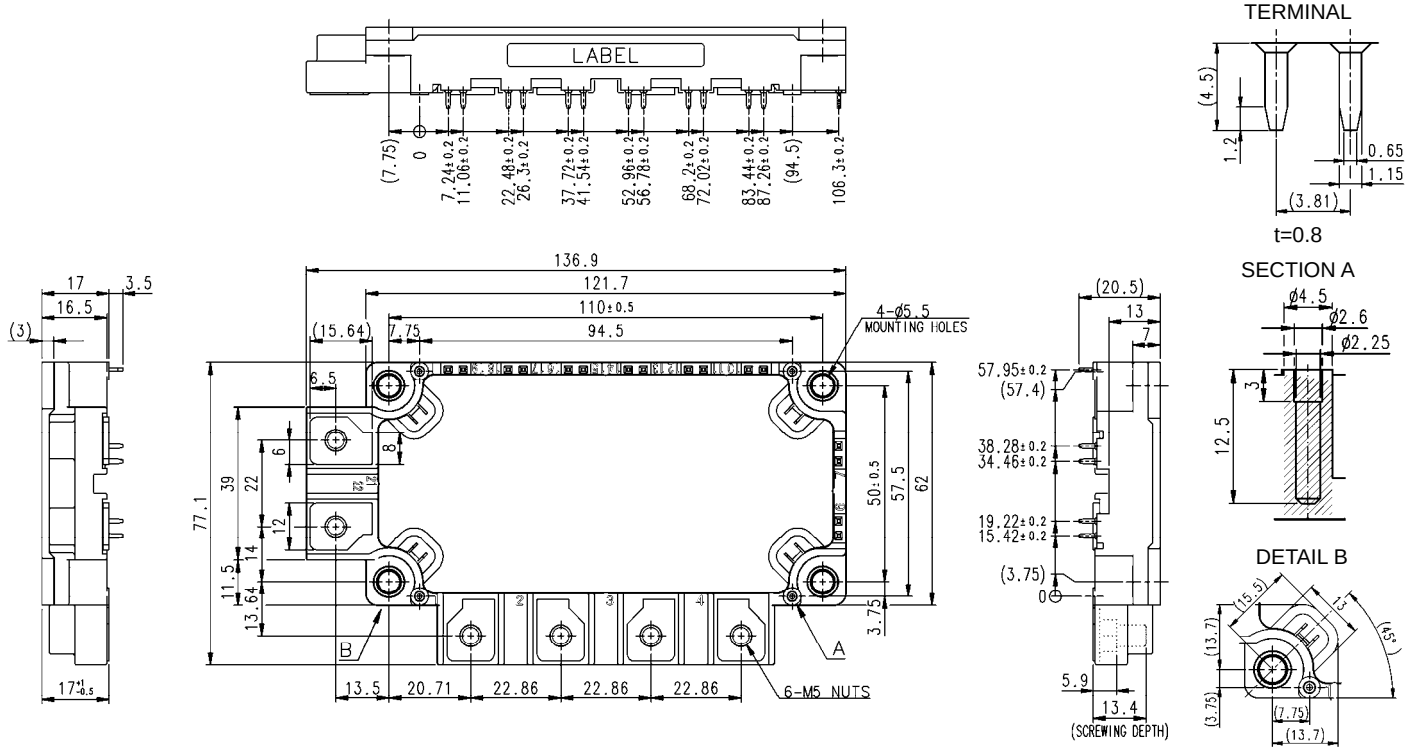
- ●Flat base Type
- ●Copper base plate (non-plating)
- ●Tin plating pin terminals
- ●RoHS Directive compliant
- ●Recognized under UL1557, File E323585

APPLICATION

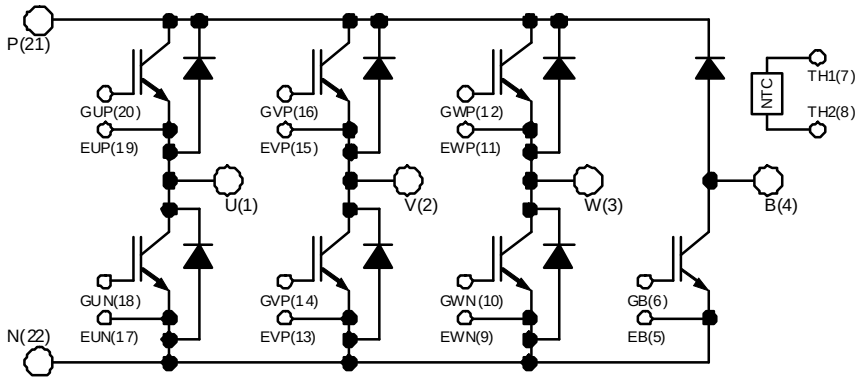
AC Motor Control, Motion/Servo Control, Power supply, etc.

OUTLINE DRAWING & INTERNAL CONNECTION

Dimension in mm



INTERNAL CONNECTION



Tolerance otherwise specified

Division of Dimension		Tolerance
0.5	to 3	±0.2
over 3	to 6	±0.3
over 6	to 30	±0.5
over 30	to 120	±0.8
over 120	to 400	±1.2

ABSOLUTE MAXIMUM RATINGS (T_j=25 °C, unless otherwise specified)

INVERTER PART IGBT/DIODE

Symbol	Item	Conditions	Rating	Unit
V_{CES}	Collector-emitter voltage	G-E short-circuited	1700	V
V_{GES}	Gate-emitter voltage	C-E short-circuited	± 20	V
I_C	Collector current	DC, T_C=125 °C (Note2, 4)	75	A
I_{CRM}		Pulse, Repetitive (Note3)	150	
P_{tot}	Total power dissipation	T_C=25 °C (Note2, 4)	830	W
I_E (Note1)	Emitter current	(Note2)	75	A
I_{ERM} (Note1)		Pulse, Repetitive (Note3)	150	

BRAKE PART IGBT/DIODE

Symbol	Item	Conditions	Rating	Unit
V_{CES}	Collector-emitter voltage	G-E short-circuited	1700	V
V_{GES}	Gate-emitter voltage	C-E short-circuited	± 20	V
I_C	Collector current	DC, T_C=125 °C (Note2, 4)	50	A
I_{CRM}		Pulse, Repetitive (Note3)	100	
P_{tot}	Total power dissipation	T_C=25 °C (Note2, 4)	600	W
V_{RRM}	Repetitive peak reverse voltage	G-E short-circuited	1700	V
I_F	Forward current	(Note2)	50	A
I_{FRM}		Pulse, Repetitive (Note3)	100	

MODULE

Symbol	Item	Conditions	Rating	Unit
V_{isol}	Isolation voltage	Terminals to base plate, RMS, f=60 Hz, AC 1 min	4000	V
T_{jmax}	Maximum junction temperature	Instantaneous event (overload)	175	°C
T_{Cmax}	Maximum case temperature	(Note4)	125	
T_{jop}	Operating junction temperature	Continuous operation (under switching)	-40 ~ +150	°C
T_{stg}	Storage temperature	-	-40 ~ +125	

ELECTRICAL CHARACTERISTICS (T_j=25 °C, unless otherwise specified)

INVERTER PART IGBT/DIODE

Symbol	Item	Conditions		Limits			Unit
				Min.	Typ.	Max.	
I_{CES}	Collector-emitter cut-off current	V_{CE}=V_{CES}, G-E short-circuited		-	-	1.0	mA
I_{GES}	Gate-emitter leakage current	V_{GE}=V_{GES}, C-E short-circuited		-	-	0.5	μA
$V_{GE(th)}$	Gate-emitter threshold voltage	I_C=7.5 mA, V_{CE}=10 V		5.4	6.0	6.6	V
V_{CEsat}	Collector-emitter saturation voltage	I_C=75 A (Note5), V_{GE}=15 V, (Terminal)	T_j=25 °C	-	2.00	2.5	V
			T_j=125 °C	-	2.20	-	
			T_j=150 °C	-	2.25	-	
		I_C=75 A (Note5), V_{GE}=15 V, (Chip)	T_j=25 °C	-	1.90	2.4	V
			T_j=125 °C	-	2.10	-	
			T_j=150 °C	-	2.15	-	
C_{ies}	Input capacitance	V_{CE}=10 V, G-E short-circuited		-	-	20	nF
C_{oes}	Output capacitance			-	-	1.6	
C_{res}	Reverse transfer capacitance			-	-	0.36	
Q_G	Gate charge	V_{CC}=1000 V, I_C=75 A, V_{GE}=15 V		-	414	-	nC
$t_{d(on)}$	Turn-on delay time	V_{CC}=1000 V, I_C=75 A, V_{GE}=±15 V, R_G=10 Ω, Inductive load		-	-	200	ns
t_r	Rise time			-	-	100	
$t_{d(off)}$	Turn-off delay time			-	-	700	
t_f	Fall time			-	-	600	

ELECTRICAL CHARACTERISTICS (cont; T_j=25 °C, unless otherwise specified)

INVERTER PART IGBT/DIODE

Symbol	Item	Conditions		Limits			Unit
				Min.	Typ.	Max.	
V_{EC} (Note1)	Emitter-collector voltage	I_E=75 A (Note5), G-E short-circuited, (Terminal)	T_j=25 °C	-	4.1	5.3	V
			T_j=125 °C	-	2.9	-	
			T_j=150 °C	-	2.7	-	
		I_E=75 A (Note5), G-E short-circuited, (Chip)	T_j=25 °C	-	4.0	5.2	V
			T_j=125 °C	-	2.8	-	
			T_j=150 °C	-	2.6	-	
t_{rr} (Note1)	Reverse recovery time	V_{CC}=1000 V, I_E=75 A, V_{GE}=±15 V, R_G=10 Ω, Inductive load		-	-	200	ns
Q_{rr} (Note1)	Reverse recovery charge			-	2.0	-	µC
E_{on}	Turn-on switching energy per pulse	V_{CC}=1000 V, I_C=I_E=75 A, V_{GE}=±15 V, R_G=10 Ω, T_j=150 °C, Inductive load		-	17.1	-	mJ
E_{off}	Turn-off switching energy per pulse			-	23	-	
E_{rr} (Note1)	Reverse recovery energy per pulse			-	15.9	-	mJ
$R_{CC'+EE'}$	Internal lead resistance	Main terminals-chip, per switch, T_C=25 °C (Note4)		-	-	4.0	mΩ
r_g	Internal gate resistance	Per switch		-	0	-	Ω

BRAKE PART IGBT/DIODE

Symbol	Item	Conditions		Limits			Unit
				Min.	Typ.	Max.	
I_{CES}	Collector-emitter cut-off current	V_{CE}=V_{CES}, G-E short-circuited		-	-	1.0	mA
I_{GES}	Gate-emitter leakage current	V_{GE}=V_{GES}, C-E short-circuited		-	-	0.5	µA
$V_{GE(th)}$	Gate-emitter threshold voltage	I_C=5 mA, V_{CE}=10 V		5.4	6.0	6.6	V
V_{CEsat}	Collector-emitter saturation voltage	I_C=50 A (Note5), V_{GE}=15 V, (Terminal)	T_j=25 °C	-	2.00	2.5	V
			T_j=125 °C	-	2.20	-	
			T_j=150 °C	-	2.25	-	
		I_C=50 A (Note5), V_{GE}=15 V, (Chip)	T_j=25 °C	-	1.90	2.4	V
			T_j=125 °C	-	2.10	-	
			T_j=150 °C	-	2.15	-	
C_{ies}	Input capacitance	V_{CE}=10 V, G-E short-circuited		-	-	13	nF
C_{oes}	Output capacitance			-	-	1.1	
C_{res}	Reverse transfer capacitance			-	-	0.24	
Q_G	Gate charge	V_{CC}=1000 V, I_C=50 A, V_{GE}=15 V		-	276	-	nC
$t_{d(on)}$	Turn-on delay time	V_{CC}=1000 V, I_C=50 A, V_{GE}=±15 V, R_G=13 Ω, Inductive load		-	-	200	ns
t_r	Rise time			-	-	100	
$t_{d(off)}$	Turn-off delay time			-	-	700	
t_f	Fall time			-	-	600	
I_{RRM}	Reverse current	V_R=V_{RRM}, G-E short-circuited		-	-	1.0	mA
V_F	Forward voltage	I_F=50 A (Note5), (Terminal)	T_j=25 °C	-	4.1	5.3	V
			T_j=125 °C	-	2.9	-	
			T_j=150 °C	-	2.7	-	
		I_F=50 A (Note5), (Chip)	T_j=25 °C	-	4.0	5.2	V
			T_j=125 °C	-	2.8	-	
			T_j=150 °C	-	2.6	-	
t_{rr}	Reverse recovery time	V_{CC}=1000 V, I_F=50 A, V_{GE}=±15 V, R_G=13 Ω, Inductive load		-	-	200	ns
Q_{rr}	Reverse recovery charge			-	1.3	-	µC
E_{on}	Turn-on switching energy per pulse	V_{CC}=1000 V, I_C=I_F=50 A, V_{GE}=±15 V, R_G=13 Ω, T_j=150 °C, Inductive load		-	9.7	-	mJ
E_{off}	Turn-off switching energy per pulse			-	11.2	-	
E_{rr}	Reverse recovery energy per pulse			-	9.8	-	mJ
r_g	Internal gate resistance	-		-	0	-	Ω

ELECTRICAL CHARACTERISTICS (cont; T_j =25 °C, unless otherwise specified)

NTC THERMISTOR PART

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
R_{25}	Zero-power resistance	T_C=25 °C (Note4)	4.85	5.00	5.15	kΩ
ΔR/R	Deviation of resistance	R_{100}=493 Ω, T_C=100 °C (Note4)	-7.3	-	+7.8	%
$B_{(25/50)}$	B-constant	Approximate by equation (Note6)	-	3375	-	K
P_{25}	Power dissipation	T_C=25 °C (Note4)	-	-	10	mW

THERMAL RESISTANCE CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
$R_{th(j-c)Q}$	Thermal resistance (Note4)	Junction to case, per Inverter IGBT	-	-	0.18	K/W
$R_{th(j-c)D}$		Junction to case, per Inverter DIODE	-	-	0.27	
$R_{th(j-c)Q}$		Junction to case, Brake IGBT	-	-	0.25	K/W
$R_{th(j-c)D}$		Junction to case, Brake DIODE	-	-	0.35	
$R_{th(c-s)}$	Contact thermal resistance (Note4)	Case to heat sink, per 1 module, Thermal grease applied (Note7)	-	15	-	K/kW

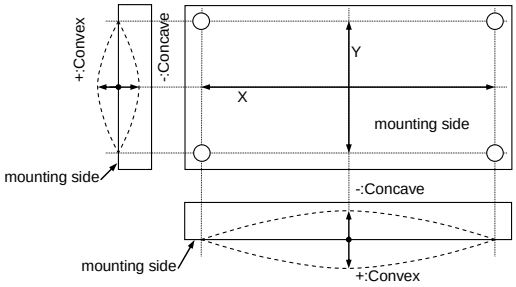
MECHANICAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
M_t	Mounting torque	Main terminals M 5 screw	2.5	3.0	3.5	N·m
M_s	Mounting torque	Mounting to heat sink M 5 screw	2.5	3.0	3.5	N·m
d_s	Creepage distance	Terminal to terminal	16.3	-	-	mm
		Terminal to base plate	16.8	-	-	
d_a	Clearance	Terminal to terminal	10	-	-	mm
		Terminal to base plate	10	-	-	
m	mass	-	-	370	-	g
e_c	Flatness of base plate	On the centerline X, Y (Note8)	±0	-	+100	μm

Note1. Represent ratings and characteristics of the anti-parallel, emitter-collector free wheeling diode (DIODE).

2. Junction temperature (T_j) should not increase beyond T_{jmax} rating.
3. Pulse width and repetition rate should be such that the device junction temperature (T_j) dose not exceed T_{jmax} rating.
4. Case temperature (T_C) and heat sink temperature (T_s) are defined on the each surface (mounting side) of base plate and heat sink just under the chips. Refer to the figure of chip location.
5. Pulse width and repetition rate should be such as to cause negligible temperature rise. Refer to the figure of test circuit.
6. $B_{(25/50)} = \ln(\frac{R_{25}}{R_{50}}) / (\frac{1}{T_{25}} - \frac{1}{T_{50}})$,

   R_{25}: resistance at absolute temperature T_{25} [K]; T_{25}=25 [°C]+273.15=298.15 [K]
   R_{50}: resistance at absolute temperature T_{50} [K]; T_{50}=50 [°C]+273.15=323.15 [K]
7. Typical value is measured by using thermally conductive grease of λ=0.9 W/(m·K).
8. The base plate (mounting side) flatness measurement points (X, Y) are as follows of the following figure.



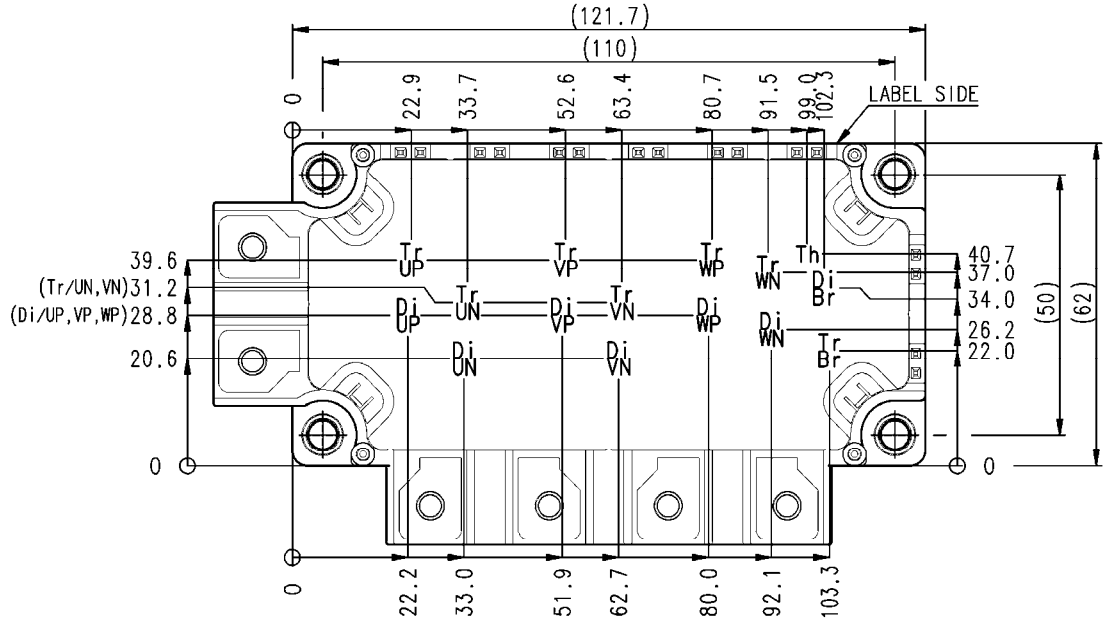
9. Use the following screws when mounting the printed circuit board (PCB) on the stand offs.
   "φ2.6×10 or φ2.6×12 self tapping screw"
   The length of the screw depends on the thickness (t1.6~t2.0) of the PCB.

RECOMMENDED OPERATING CONDITIONS

Symbol	Item	Conditions		Limits			Unit
				Min.	Typ.	Max.	
V_{CC}	(DC) Supply voltage	Applied across P-N terminals		-	1000	1200	V
V_{GEon}	Gate (-emitter drive) voltage	Applied across GB-EB/ G*P-E*P/G*N-E*N(*=U, V, W) terminals		13.5	15.0	16.5	V
R_G	External gate resistance	Per switch	Inverter IGBT	10	-	100	Ω
			Brake IGBT	13	-	130	

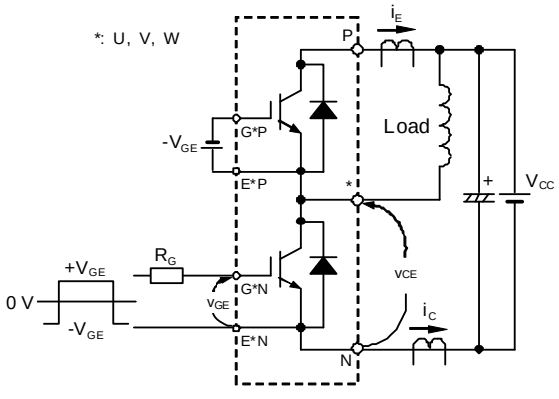
CHIP LOCATION (Top view)

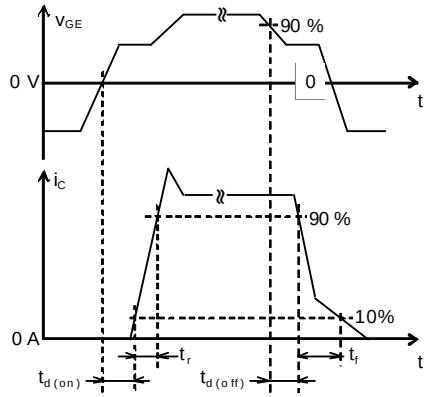
Dimension in mm, tolerance: ±1 mm



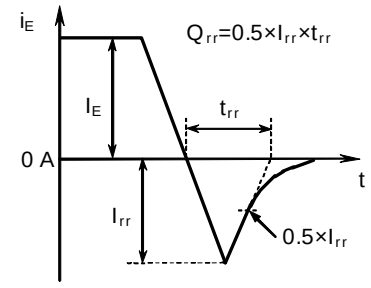
Tr*P/Tr*N/TrBr: IGBT, Di*P/Di*N: DIODE (*=U/V/W), DiBr: BRAKE DIODE, Th: NTC thermistor

TEST CIRCUIT AND WAVEFORMS

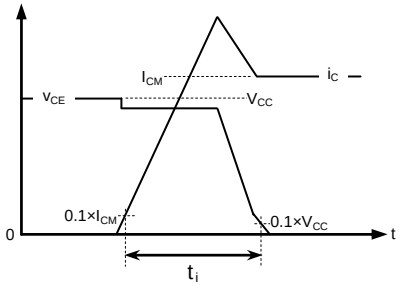




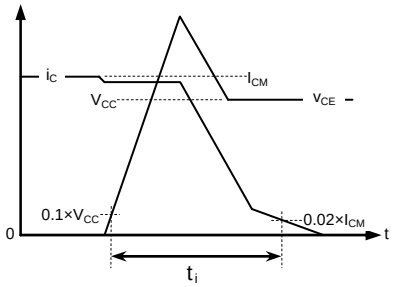
Switching test circuit and waveforms



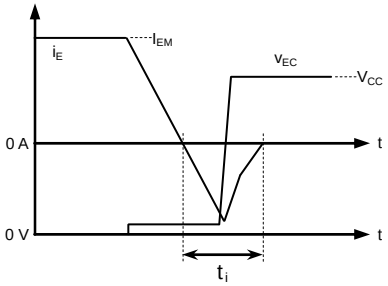
t_{rr}, Q_{rr} test waveform



IGBT Turn-on switching energy



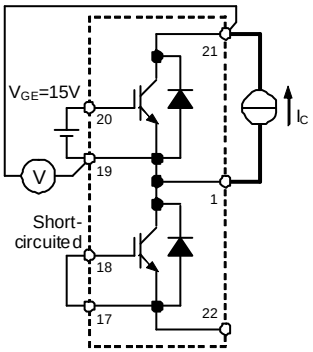
IGBT Turn-off switching energy

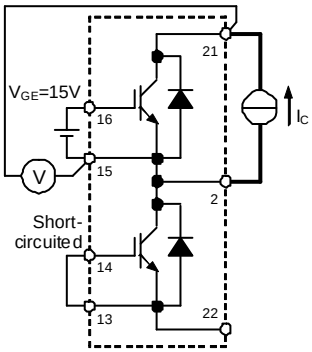


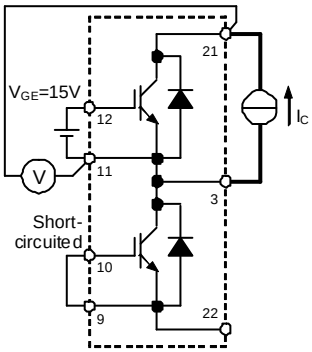
DIODE Reverse recovery energy

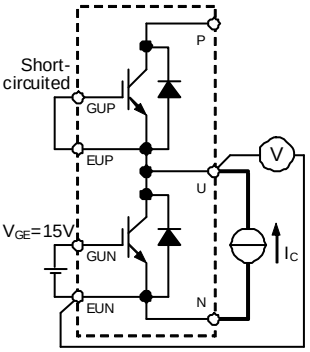
Turn-on / Turn-off switching energy and Reverse recovery energy test waveforms (Integral time instruction drawing)

TEST CIRCUIT



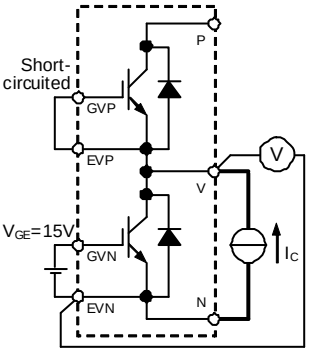






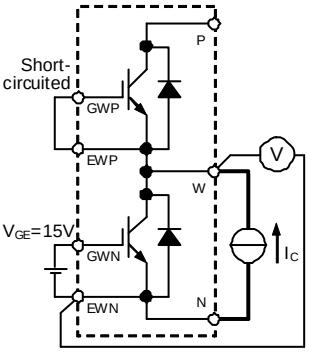
Gate-emitter short-circuited: GVP-EVP GVN-EVN, GWP-EWP, GWN-EWN, GB-EB

UP / UN IGBT



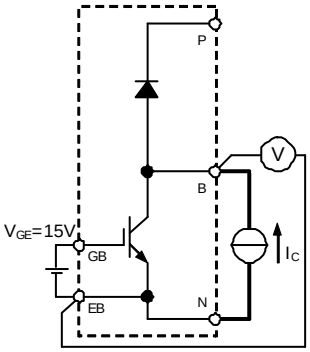
Gate-emitter short-circuited: GUP-EUP, GUN-EUN, GWP-EWP, GWN-EWN, GB-EB

VP / VN IGBT



Gate-emitter short-circuited: GUP-EUP, GUN-EUN, GVP-EVP, GVN-EVN, GB-EB

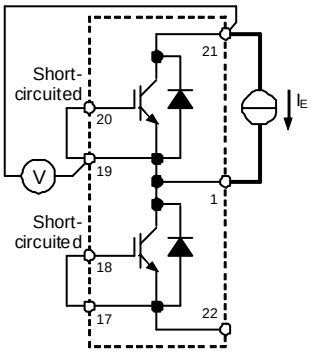
WP / WN IGBT

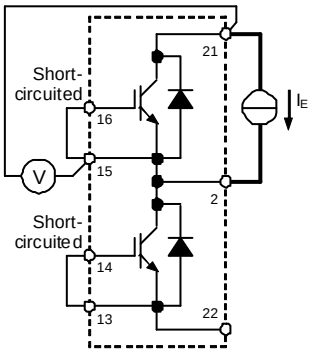


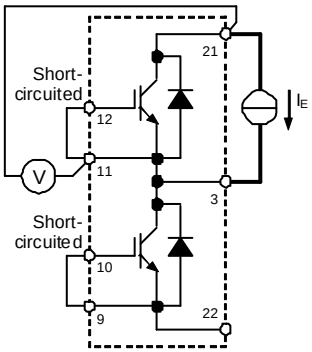
Gate-emitter short-circuited: GUP-EUP, GUN-EUN, GVP-EVP, GVN-EVN, GWP-EWP, GWN-EWN

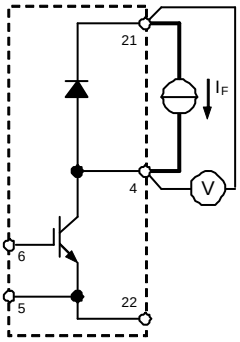
Brake IGBT

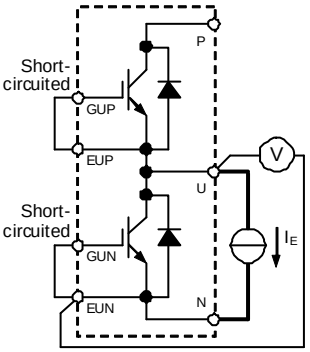
V_{CEsat} test circuit





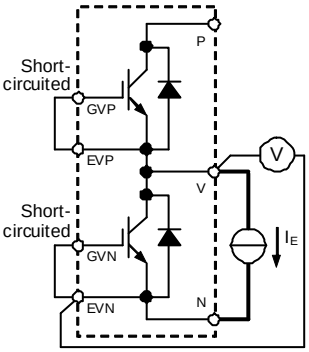






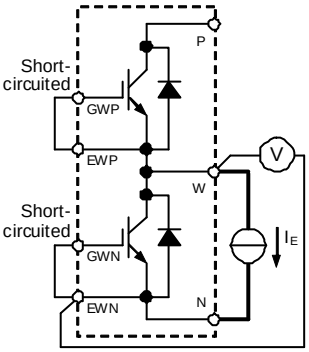
Gate-emitter short-circuited: GVP-EVP GVN-EVN, GWP-EWP, GWN-EWN, GB-EB

UP / UN DIODE



Gate-emitter short-circuited: GUP-EUP, GUN-EUN, GWP-EWP, GWN-EWN, GB-EB

VP / VN DIODE



Gate-emitter short-circuited: GUP-EUP, GUN-EUN, GVP-EVP, GVN-EVN, GB-EB

WP / WN DIODE

Gate-emitter short-circuited: GUP-EUP, GUN-EUN, GVP-EVP, GVN-EVN, GWP-EWP, GWN-EWN

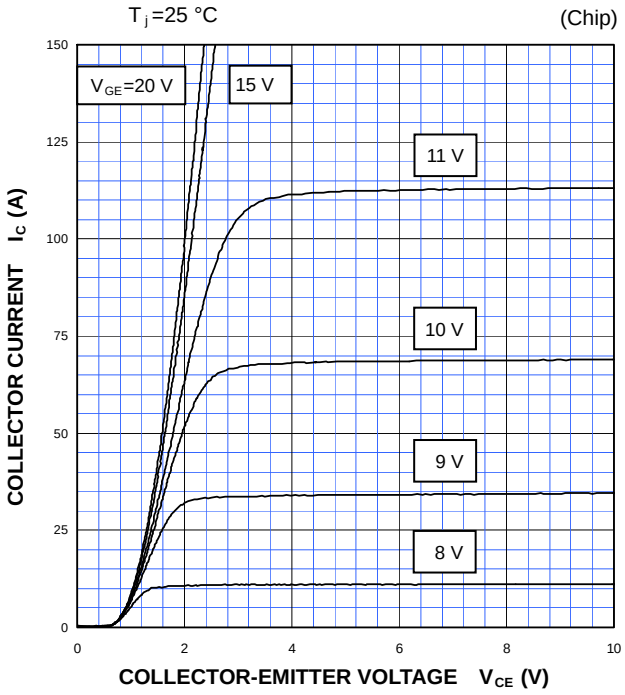
Brake DIODE

V_{EC} / V_F test circuit

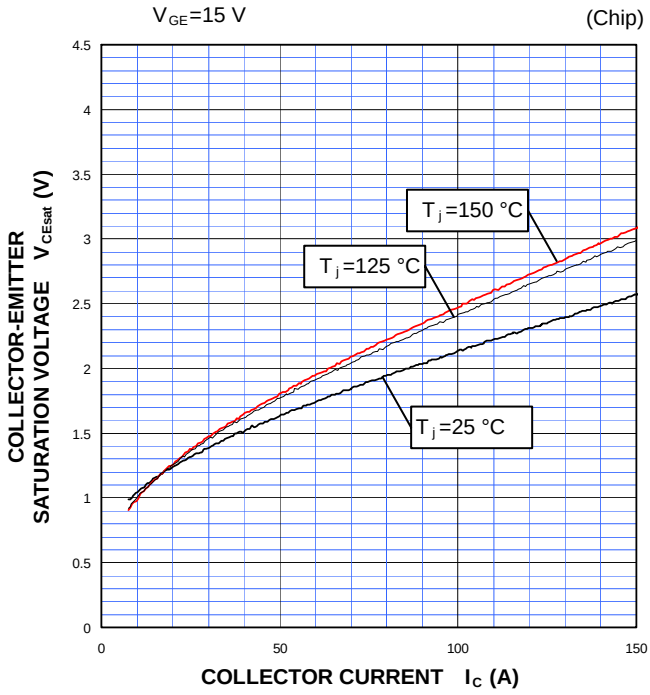
PERFORMANCE CURVES

INVERTER PART

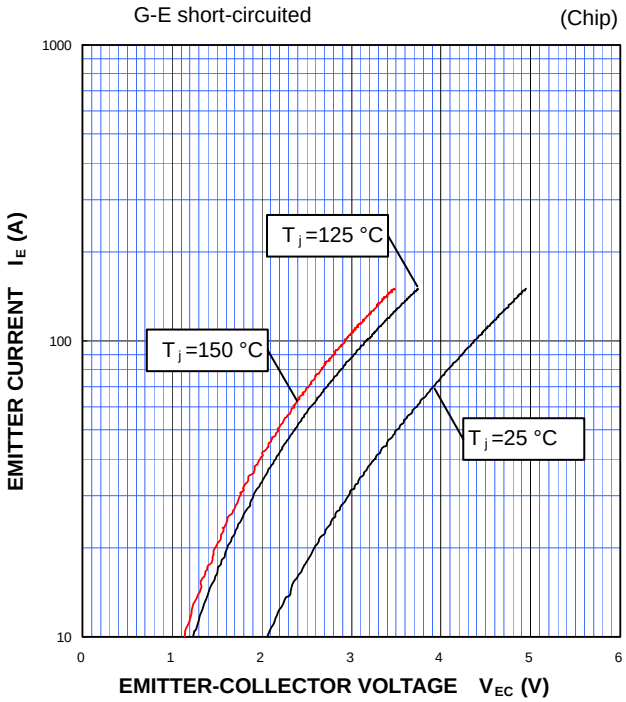
OUTPUT CHARACTERISTICS (TYPICAL)



COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



FREE WHEELING DIODE FORWARD CHARACTERISTICS (TYPICAL)

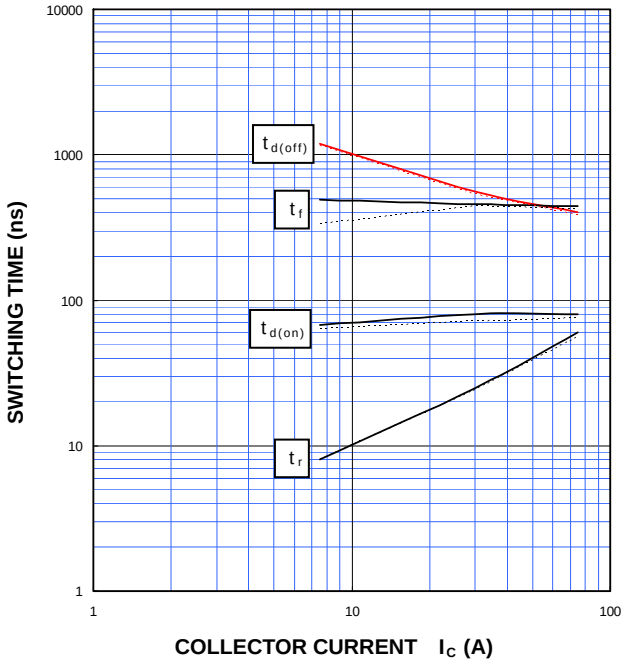


PERFORMANCE CURVES

INVERTER PART

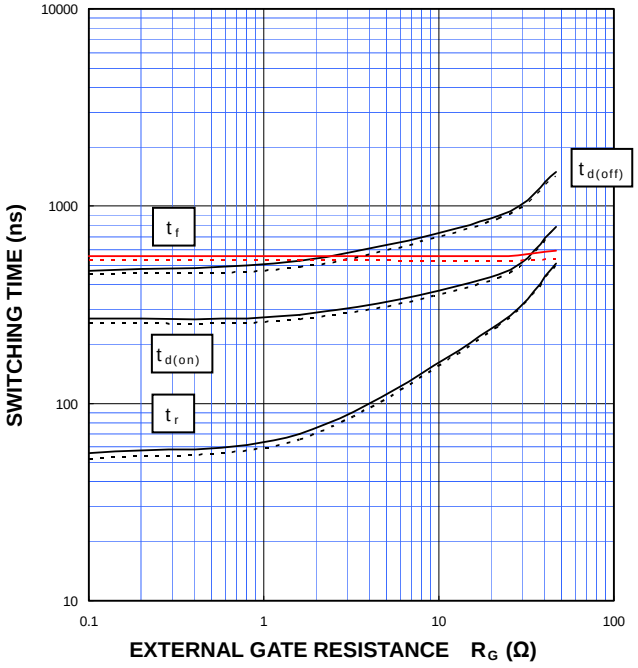
**HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)**

V_{CC}=1000 V, V_{GE}=±15 V, R_G=10 Ω, INDUCTIVE LOAD
———: T_j=150 °C, - - - - -: T_j=125 °C



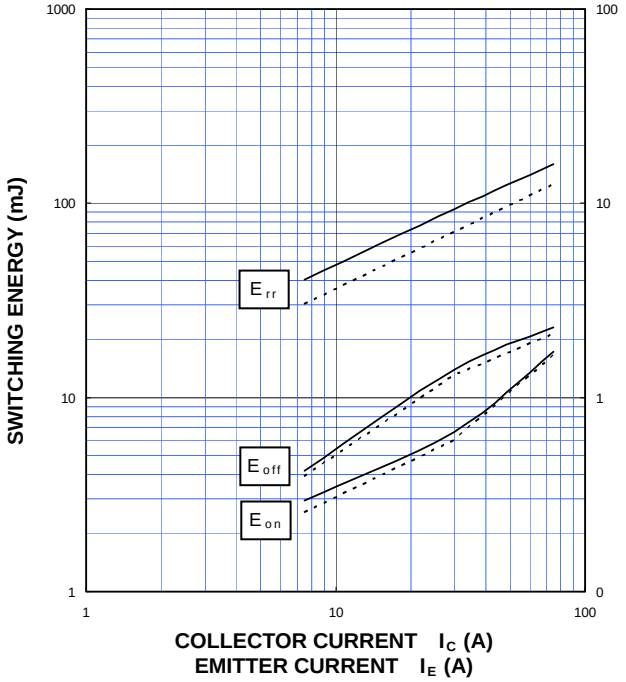
**HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)**

V_{CC}=1000 V, V_{GE}=±15 V, I_C=75 A, INDUCTIVE LOAD
———: T_j=150 °C, - - - - -: T_j=125 °C



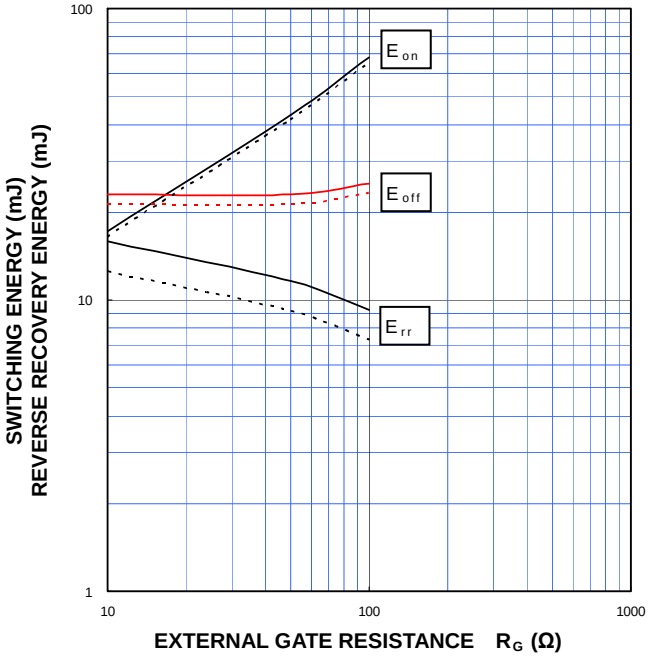
**HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)**

V_{CC}=1000 V, V_{GE}=±15 V, R_G=10 Ω,
INDUCTIVE LOAD, PER PULSE
———: T_j=150 °C, - - - - -: T_j=125 °C



**HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)**

V_{CC}=1000 V, V_{GE}=±15 V, I_C/I_E=75 A,
INDUCTIVE LOAD, PER PULSE
———: T_j=150 °C, - - - - -: T_j=125 °C

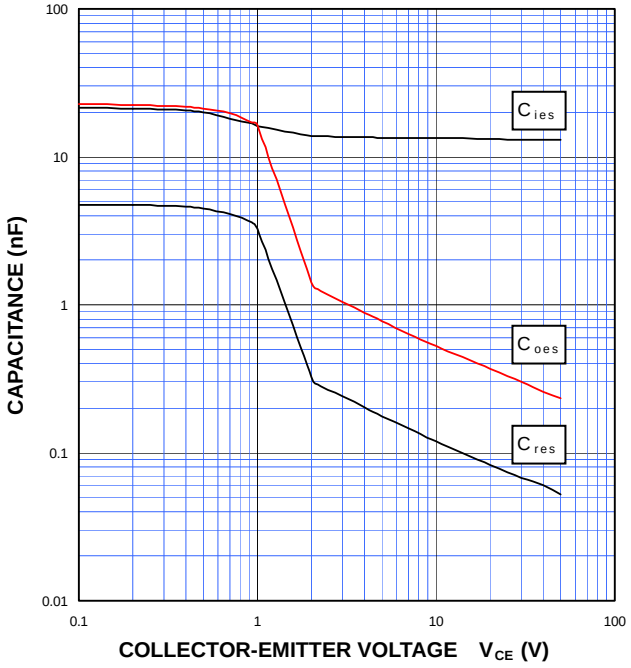


PERFORMANCE CURVES

INVERTER PART

CAPACITANCE CHARACTERISTICS (TYPICAL)

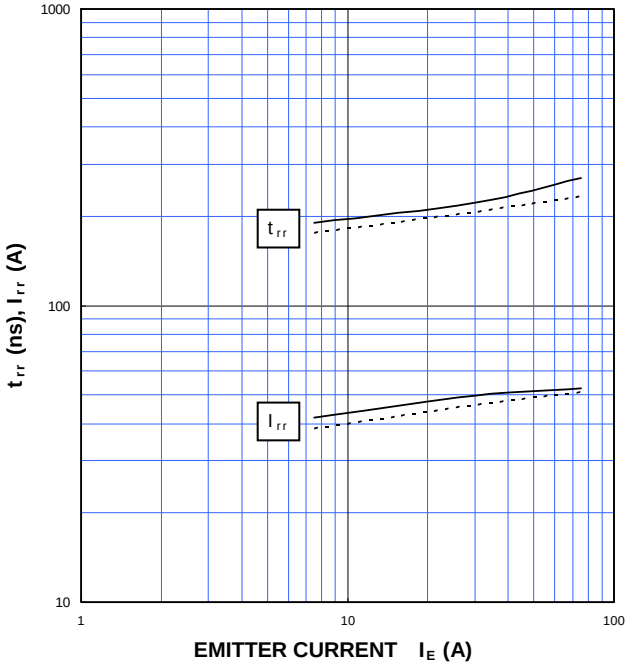
G-E short-circuited, T_j=25 °C



FREE WHEELING DIODE REVERSE RECOVERY CHARACTERISTICS (TYPICAL)

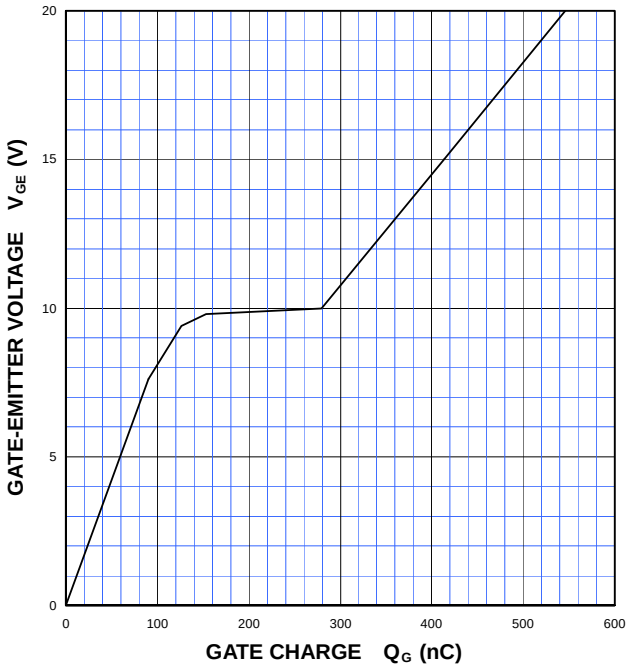
V_{CC}=1000 V, V_{GE}=±15 V, R_G=10 Ω, INDUCTIVE LOAD

———: T_j=150 °C, - - - - -: T_j=125 °C



GATE CHARGE CHARACTERISTICS (TYPICAL)

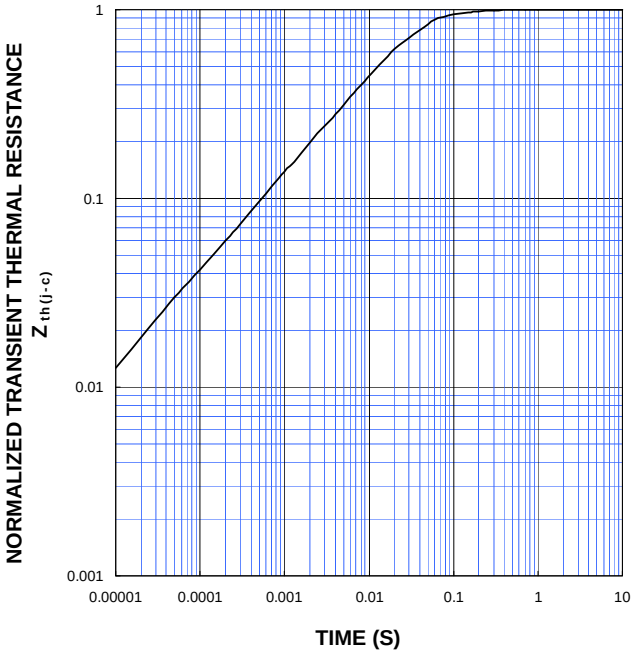
V_{CC}=1000 V, I_C=75 A, T_j=25 °C



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (MAXIMUM)

Single pulse, T_C=25 °C

$R_{th(j-c)Q}$=0.18 K/W, $R_{th(j-c)D}$=0.27 K/W

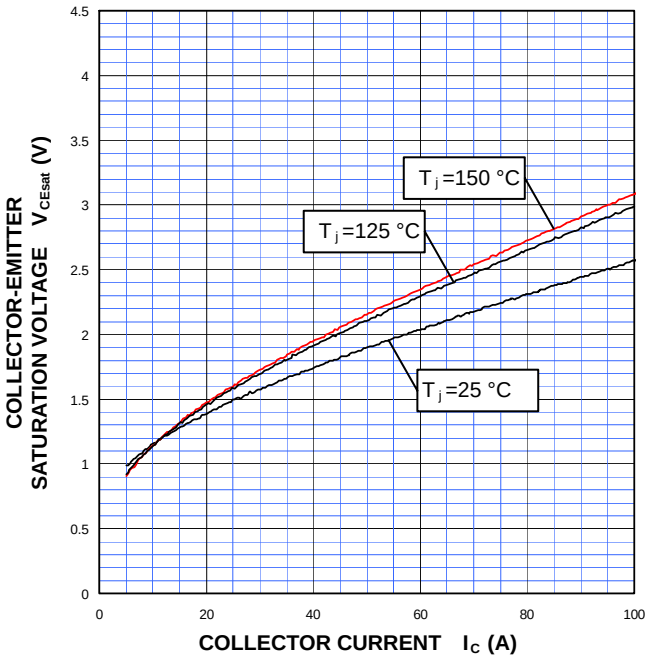


PERFORMANCE CURVES

BRAKE PART

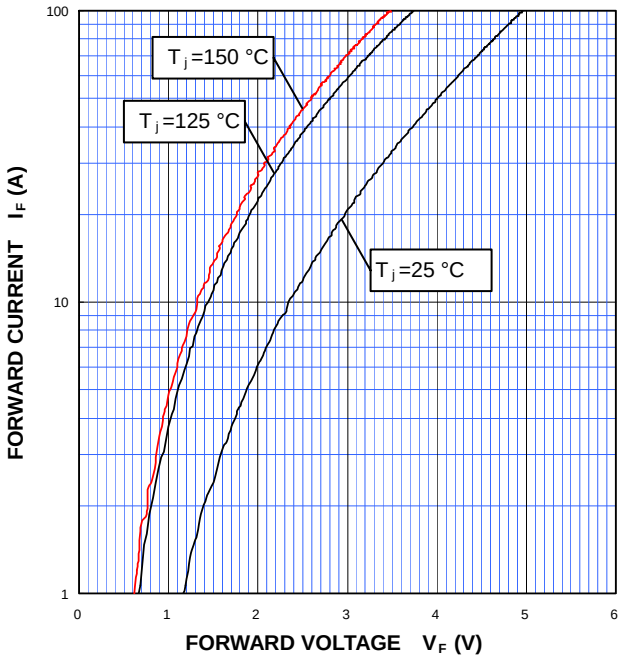
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)

V_{GE}=15 V (Chip)



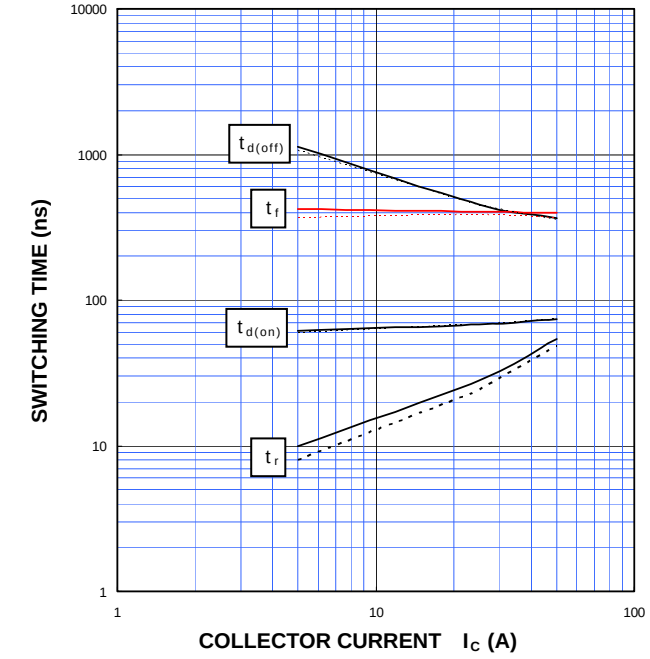
CLAMP DIODE FORWARD CHARACTERISTICS (TYPICAL)

G-E short-circuited (Chip)



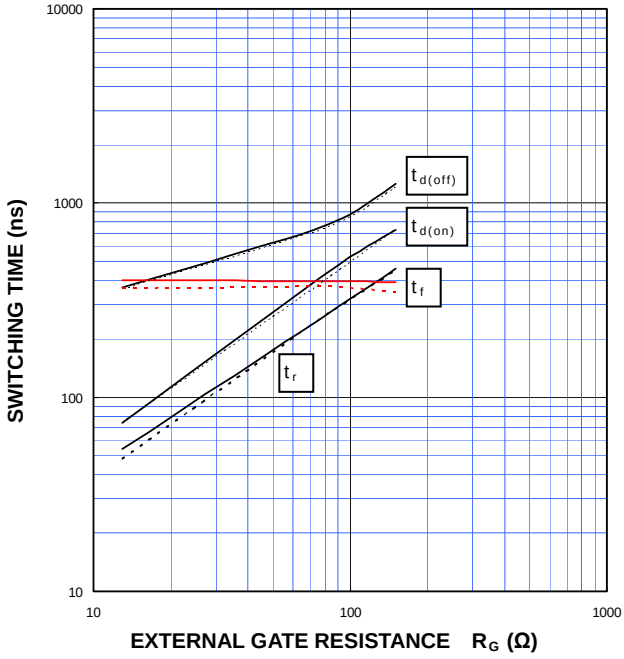
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

V_{CC}=1000 V, V_{GE}=±15 V, R_G=13 Ω, INDUCTIVE LOAD
———: T_j=150 °C, - - - - -: T_j=125 °C



HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

V_{CC}=1000 V, I_C=50 A, V_{GE}=±15 V, INDUCTIVE LOAD
———: T_j=150 °C, - - - - -: T_j=125 °C

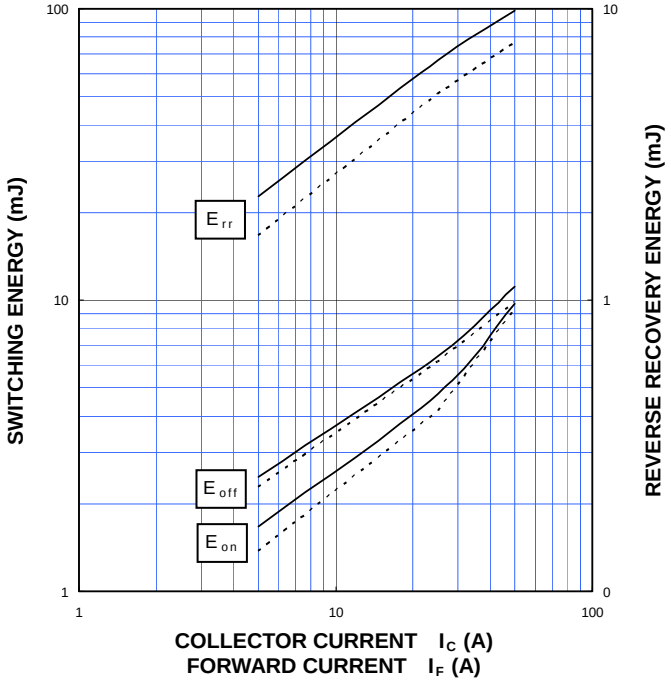


PERFORMANCE CURVES

BRAKE PART

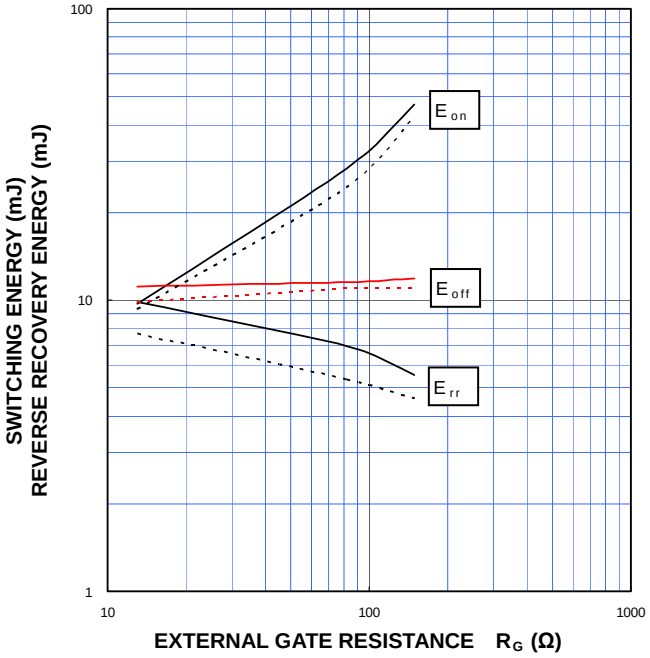
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

V_{CC}=1000 V, V_{GE}=±15 V, R_G=13 Ω,
INDUCTIVE LOAD, PER PULSE
———: T_j=150 °C, - - - - -: T_j=125 °C



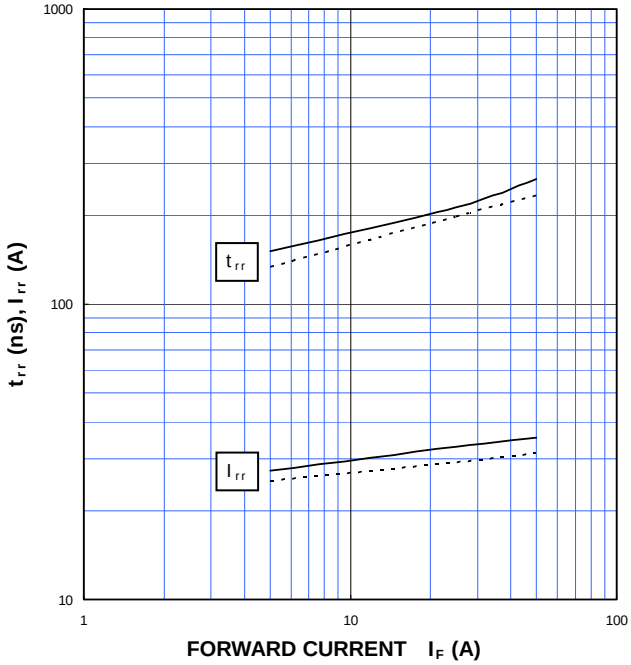
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

V_{CC}=1000 V, I_C/I_F=50 A, V_{GE}=±15 V,
INDUCTIVE LOAD, PER PULSE
———: T_j=150 °C, - - - - -: T_j=125 °C



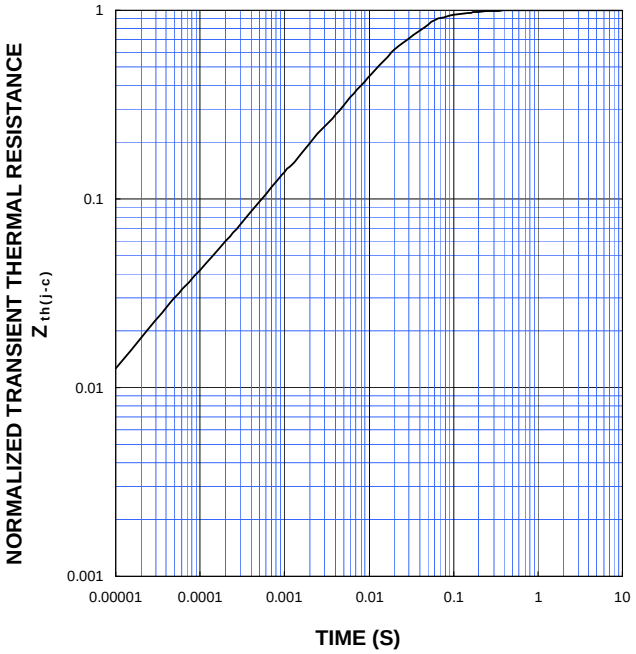
CLAMP DIODE REVERSE RECOVERY CHARACTERISTICS (TYPICAL)

V_{CC}=1000 V, V_{GE}=±15 V, R_G=13 Ω, INDUCTIVE LOAD
———: T_j=150 °C, - - - - -: T_j=125 °C



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (MAXIMUM)

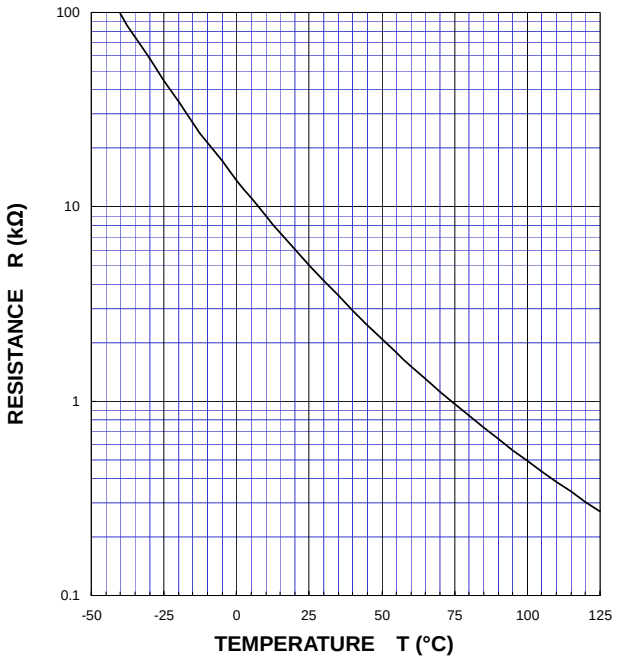
Single pulse, T_C=25 °C
$R_{th(j-c)Q}$=0.25 K/W, $R_{th(j-c)D}$=0.35 K/W



PERFORMANCE CURVES

NTC thermistor part

TEMPERATURE CHARACTERISTICS
(TYPICAL)



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